

NBM[™] in a VIA Package Bus Converter

NBM3814x60E12A7yzz



Non-Isolated, Fixed-Ratio DC-DC Converter

Features & Benefits

- Up to 170 A continuous secondary output current
- Fixed transformation ratio(K) of 1/5
- Up to 1046 W/in³ power density
- 97.8% peak efficiency
- · Bidirectional operation capability
- · Input & output ceramic capacitance filtering
- · Parallel operation for multi-kW arrays
- · OV, OC, UV, short circuit and thermal protection
- 3814 package
- High MTBF
- Thermally enhanced VIA[™] package

Typical Applications

- DC Power Distribution
- Information and Communication Technology (ICT) Equipment
- High End Computing Systems
- Automated Test Equipment
- · Industrial Systems
- High Density Energy Systems
- Transportation



Product Ratings						
V _{PRI} = 54 V (36 – 60 V)	I_{SEC} = up to 170 A					
V _{SEC} = 10.8 V (7.2 – 12.0 V) (NO LOAD)	K = 1/5					

Product Description

The NBM in a VIA package is a high efficiency Bus Converter, operating from a 36 to 60 V_{DC} primary bus to deliver a non-isolated 7.2 to 12 V_{DC} unregulated, secondary output.

This unique ultra-low profile module incorporates DC-DC conversion, integrated filtering in a chassis or PCB mount form factor.

The NBM offers low noise, fast transient response and industry leading efficiency and power density.

Leveraging the thermal and density benefits of Vicor's VIA packaging technology, the NBM module offers flexible thermal management options with very low top and bottom side thermal impedances.

When combined with downstream Vicor DC-DC conversion components and regulators, the NBM allows the Power Design Engineer to employ a simple, low-profile design which will differentiate the end system without compromising on cost or performance metrics.

The NBM non-isolated topology allows start up and steady state operation in forward and reverse directions. It provides bidirectional protections. However if power train is disabled by any protection, and V_{SEC} is present, then voltage equal to V_{SEC} minus two diode drops will appear on primary side.

Part Ordering Information

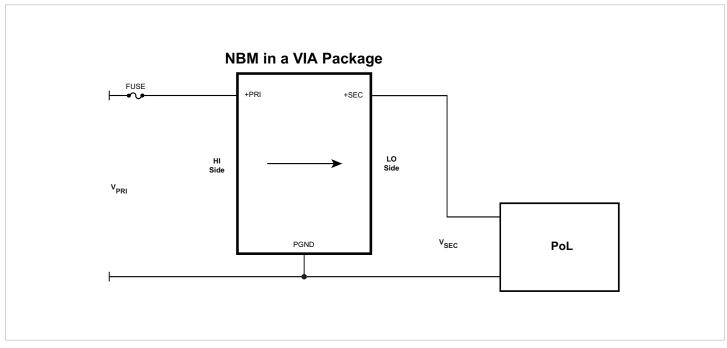
3.76 x 1.40 x 0.37 in 95.59 x 35.54 x 9.40 mm

Product Function	Package Length	Package Width	Package Type	Max Primary Input Voltage	Primary Input Range Ratio	Max Secondary Output Voltage	Max Secondary Output Current	Product Grade (Case Temperature)	Option Field
NBM	38	14	Х	60	Е	12	A7	у	ZZ
NBM = Non-Isolated Bus Converter Module	Length in Inches x 10	Width in Inches x 10	B = Board VIA V = Chassis VIA	Internal Reference		$C = -20 \text{ to } 100^{\circ}C^{[1]}$ $T = -40 \text{ to } 100^{\circ}C^{[1]}$	00 = Chassis/Always On 04 = Short Pin/Always On 08 = Long Pin/Always On		

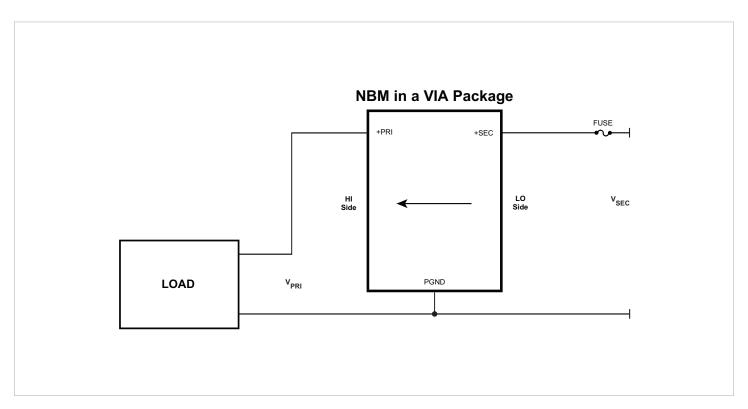
^[1] High Temperature Current Derating may apply; See Figure 1, specified thermal operating area.



Typical Application



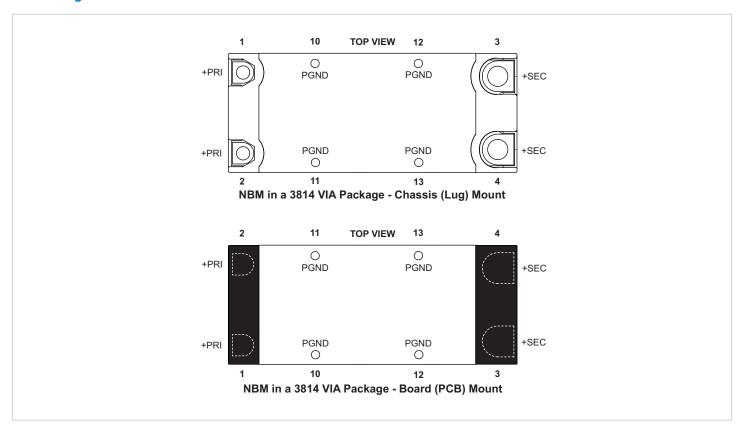
NBM3814x60E12A7yzz at point of load providing fixed ratio step-down DC-DC conversion to PoL devices. NBM is operating in forward direction.



NBM3814x60E12A7yzz providing fixed ratio step-up DC-DC conversion. NBM is operating in reverse direction.



Pin Configuration



Pin Descriptions

Pin Number	Pin Number Signal Name Type		Function
1, 2	+PRI	PRIMARY POWER	Positive primary transformer power terminal - HI side
3, 4 +SEC SECONDARY POWER			Positive secondary transformer power terminal - LO side
10, 11, 12, 13	PGND	POWER RETURN	Negative transformer power terminal - HI side and LO side



Absolute Maximum Ratings

The absolute maximum ratings below are stress ratings only. Operation at or beyond these maximum ratings can cause permanent damage to the device.

Parameter	Comments	Min	Max	Unit
+PRI to PGND		-1	80	V
PRI_DC or SEC_DC slew rate			1	V/µs
+SEC to PGND		-1	16	V
Dielectric Withstand*	See note below			
Primary-Case		N/A		Vdc
Primary-Secondary		N/A		Vdc
Secondary-Case		N/A		Vdc

^{*} The PGND of the NBM in a VIA package is directly connected to the case. The NBM does not contain any insulation (isolation) from Input (Primary) to Output (Secondary).



Electrical Specifications

Specifications apply over all line and load conditions, unless otherwise noted; **Boldface** specifications apply over the temperature range of -40°C \leq T_{CASE} \leq 100°C (T-Grade); All other specifications are at T_{CASE} = 25°C unless otherwise noted.

Attribute	Symbol	Conditions / Notes	Min	Тур	Max	Unit	
General Powetrain PRIMARY to SECONDARY Specification (Forward Direction)							
Primary Input Voltage range, continuous	V _{PRI_DC}		36		60	V	
V _{PRI} µController	$V_{\mu C_ACTIVE}$	V_{PRLDC} voltage where μC is initialized, (powertrain inactive)			15	V	
PRI to SEC Input Quiescent Current	I	Disabled, V _{PRI_DC} = 54 V		7		mA	
Fix to SEC input Quiescent Current	I _{PRI_Q}	$T_{CASE} \le 100^{\circ}C$			12	IIIA	
		$V_{PRI_DC} = 54 \text{ V}, T_{CASE} = 25^{\circ}\text{C}$		10	12		
PRI to SEC No Load Power	D	$V_{PRI_DC} = 54 \text{ V}$	8		19	W	
Dissipation	P _{PRI_NL}	V _{PRI_DC} = 36 V to 60 V, T _{CASE} = 25 °C			14	VV	
		V _{PRI_DC} = 36 V to 60 V			22		
PRI to SEC Inrush Current Peak	I _{PRI_INR_PK}	V_{PRI_DC} = 60 V, C_{SEC_EXT} = 3000 $\mu\text{F},~R_{LOAD_SEC}$ = 20% of full load current		15		А	
		T _{CASE} ≤ 100°C		50	50		
DC Primary Input Current	I _{PRI_IN_DC}	At I _{SEC_OUT_DC} = 170 A, T _{CASE} ≤ 90°C			34.4	А	
Transformation Ratio	K	Primary to secondary, $K = V_{SEC_DC} / V_{PRI_DC}$, at no load		1/5		V/V	
Secondary Output Current (continuous)	I _{SEC_OUT_DC}	T _{CASE} ≤ 90°C			170	А	
Secondary Output Current (pulsed)	I _{SEC_OUT_PULSE}	10 ms pulse, 25% Duty cycle, I _{SEC_OUT_AVG} ≤ 50% rated I _{SEC_OUT_DC}			200	А	
		$V_{PRI_DC} = 54 \text{ V}, I_{SEC_OUT_DC} = 170 \text{ A}$	96.5	97			
PRI to SEC Efficiency (ambient)	η_{AMB}	V_{PRI_DC} = 36 V to 60 V, $I_{SEC_OUT_DC}$ = 170 A	95.6			%	
		$V_{PRI_DC} = 54 \text{ V}, I_{SEC_OUT_DC} = 85 \text{ A}$	97.3	97.8			
PRI to SEC Efficiency (hot)	η_{HOT}	$V_{PRI_DC} = 54 \text{ V}, I_{SEC_OUT_DC} = 170 \text{ A}, T_{CASE} = 90^{\circ}\text{C}$	96.2	96.5		%	
PRI to SEC Efficiency (over load range)	η _{20%}	34 A < I _{SEC_OUT_DC} < 170 A	95			%	
	R _{SEC_COLD}	$V_{PRI_DC} = 54 \text{ V}, I_{SEC_OUT_DC} = 170 \text{ A}, T_{CASE} = -40^{\circ}\text{C}$	0.5	1.1	1.5		
PRI to SEC Output Resistance	R _{SEC_AMB}	$V_{PRI_DC} = 54 \text{ V}, I_{SEC_OUT_DC} = 170 \text{ A}$	8.0	1.3	1.8	$m\Omega$	
	R _{SEC_HOT}	V _{PRI_DC} = 54 V, I _{SEC_OUT_DC} = 170 A, T _{CASE} = 90°C	1.1	1.7	2.0		
Switching Frequency	F _{SW}	Frequency of the Output Voltage Ripple = 2x F _{SW}	1.02	1.07	1.12	MHz	
Secondary Output Voltage Ripple	V _{SEC} OUT PP	$C_{SEC_EXT} = 0 \mu F$, $I_{SEC_OUT_DC} = 170 \text{ A}$, $V_{PRI_DC} = 54 \text{ V}$, 20 MHz BW		125		mV	
		T _{CASE} ≤ 100°C			400		



Electrical Specifications (Cont.)

Specifications apply over all line and load conditions, unless otherwise noted; **Boldface** specifications apply over the temperature range of $-40^{\circ}\text{C} \leq T_{CASE} \leq 100^{\circ}\text{C}$ (T-Grade); All other specifications are at $T_{CASE} = 25^{\circ}\text{C}$ unless otherwise noted.

Attribute	Symbol	Conditions / Notes	Min	Тур	Max	Unit
	eral Powetrain I	PRIMARY to SECONDARY Specification (Forward Dire	ection) Co	nt.		
Effective Primary Capacitance (Internal)	C _{PRI_INT}	Effective Value at 54 V _{PRI_DC}		16.80		μF
Effective Secondary Capacitance (Internal)	C _{SEC_INT}	Effective Value at 10.8 V _{SEC_DC}		140		μF
Effective Secondary Output Capacitance (External)	C _{SEC_OUT_EXT}	Excessive capacitance may drive module into SC protection			3000	μF
Effective Secondary Output Capacitance (External)	C _{SEC_OUT_AEXT}	$C_{SEC_OUT_AEXT}$ Max = N * 0.5 * $C_{SEC_OUT_EXT\ MAX}$, where N = the number of units in parallel				
	Protec	tion PRIMARY to SECONDARY (Forward Direction)				
A. I. Dudad Time		Startup into a persistent fault condition. Non-Latching	040		4040	
Auto Restart Time	t _{AUTO_RESTART}	fault detection given $V_{PRI_DC} > V_{PRI_UVLO+}$	940		1010	ms
Primary Overvoltage Lockout Threshold	V _{PRI_OVLO+}		63	66	69	V
Primary Overvoltage Recovery Threshold	V _{PRI_OVLO} -		60	63	66	V
Primary Overvoltage Lockout Hysteresis	V _{PRI_OVLO_HYST}			3		V
Primary Overvoltage Lockout Response Time	t _{PRI_OVLO}			30		μs
Primary Undervoltage Lockout Threshold	V _{PRI_UVLO} -		28	30	32	V
Primary Undervoltage Recovery Threshold	V _{PRI_UVLO+}		32	34	36	V
Primary Undervoltage Lockout Hysteresis	V _{PRI_UVLO_HYST}			4		V
Primary Undervoltage Lockout Response Time	t _{PRI_UVLO}			100		μs
Primary Undervoltage Startup Delay	t _{PRI_UVLO+_DELAY}	From $V_{PRI_DC} = V_{PRI_UVLO+}$ to powertrain active, (i.e One time Startup delay form application of V_{PRI_DC} to V_{SEC_DC})		30		ms
Primary Soft-Start Time	t _{PRI_SOFT} -START	From powertrain active. Fast Current limit protection disabled during Soft-Start		1		ms
Secondary Output Overcurrent Trip Threshold	I _{SEC_OUT_OCP}	-	201	220	250	А
Secondary Output Overcurrent Response Time Constant	t _{SEC_OUT_OCP}	Effective internal RC filter		4		ms
Secondary Output Short Circuit Protection Trip Threshold	I _{SEC_OUT_SCP}		250			А
Secondary Output Short Circuit Protection Response Time	t _{SEC_OUT_SCP}			1		μs
Overtemperature Shutdown Threshold	t _{OTP+}	Temperature sensor located inside controller IC	125			°C
Overtemperature Recovery Threshold	t _{OTP}		105	110	115	°C
Undertemperature Shutdown Threshold	t _{UTP}	Temperature sensor located inside controller IC; Protection not available for M-Grade units.			-45	°C
Undertemperature Restart Time	t _{UTP_RESTART}	Startup into a persistent fault condition. Non-Latching fault detection given $V_{PRI_DC} > V_{PRI_UVLO+}$		3		S



Electrical Specifications (Cont.)

Specifications apply over all line and load conditions, unless otherwise noted; **Boldface** specifications apply over the temperature range of $-40^{\circ}\text{C} \leq T_{CASE} \leq 100^{\circ}\text{C}$ (T-Grade); All other specifications are at $T_{CASE} = 25^{\circ}\text{C}$ unless otherwise noted.

Attribute	Symbol	Conditions / Notes	Min	Тур	Max	Unit
Ge	eneral Powetra	ain SECONDARY to PRIMARY Specification (Reverse	Direction)			
Secondary Input Voltage range, continuous	V _{SEC_DC}		7.2		12.0	V
		$V_{SEC_DC} = 10.8 \text{ V}, T_{CASE} = 25^{\circ}\text{C}$		10	12	
SEC to PRI No Load Power	D	$V_{SEC_DC} = 10.8 \text{ V}$	8.0		19	W
Dissipation	P _{SEC_NL}	V _{SEC_DC} = 7.2 V to 12.0 V, T _{CASE} = 25°C			14	VV
		V _{SEC_DC} = 7.2 V to 12.0 V			22	
DC Secondary Input Current	I _{SEC_IN_DC}	At $I_{PRI_DC} = 34$ A, $T_{CASE} \le 90^{\circ}$ C			172	А
Primary Output Current (continuous)	I _{PRI_OUT_DC}	T _{CASE} ≤ 90°C			34	А
Primary Output Current (pulsed)	I _{PRI_OUT_PULSE}	10 ms pulse, 25% Duty cycle, I _{PRI_OUT_AVG} ≤ 50% rated I _{PRI_OUT_DC}			40.8	А
		$V_{SEC_DC} = 10.8 \text{ V, } I_{PRI_OUT_DC} = 34 \text{ A}$	96.1	96.6		
SEC to PRI Efficiency (ambient)	η_{AMB}	V _{SEC_DC} = 7.2 V to 12.0 V, I _{PRI_OUT_DC} = 34 A	95.2			%
		V _{SEC_DC} = 10.8 V, I _{PRI_OUT_DC} = 17 A	97.3	97.8		
SEC to PRI Efficiency (hot)	η_{HOT}	V _{SEC_DC} = 10.8 V, I _{PRI_OUT_DC} = 34 A, T _{CASE} = 90°C	95.8	96.1		%
SEC to PRI Efficiency (over load range)	η _{20%}	6.80 A < I _{PRI_OUT_DC} < 34 A	94.5			%
	R _{PRI_COLD}	V _{SEC_DC} = 10.8 V, I _{PRI_OUT_DC} = 34 A, T _{CASE} = -40°C	22	39	49	
SEC to PRI Output Resistance	R _{PRI_AMB}	V _{SEC_DC} = 10.8 V, I _{PRI_OUT_DC} = 34 A	28	49	72	$m\Omega$
	R _{PRI_HOT}	V _{SEC_DC} = 10.8 V, I _{PRI_OUT_DC} = 34 A, T _{CASE} = 90°C	36	58	70	
Primary Output Voltage Ripple	V _{PRI OUT PP}	$C_{PRI_OUT_EXT} = 0 \mu F$, $I_{PRI_OUT_DC} = 34 A$, $V_{SEC_DC} = 10.8 V$, 20 MHz BW		625		mV
	1111_001_11	T _{CASE} ≤ 100°C			1500	1



Electrical Specifications (Cont.)

Specifications apply over all line and load conditions, unless otherwise noted; **Boldface** specifications apply over the temperature range of $-40^{\circ}\text{C} \leq T_{CASE} \leq 100^{\circ}\text{C}$ (T-Grade); All other specifications are at $T_{CASE} = 25^{\circ}\text{C}$ unless otherwise noted.

Attribute	Symbol	Conditions / Notes	Min	Тур	Max	Unit
	Prote	ction SECONDARY to PRIMARY (Reverse Direction)				
Effective Primary Output Capacitance (External)	C _{PRI_OUT_EXT}	Excessive capacitance may drive module into SC protection when starting from Secondary to Primary			100	μF
Secondary Overvoltage Lockout Threshold	V _{SEC_OVLO+}		12.8	13.2	13.6	V
Secondary Overvoltage Recovery Threshold	V_{PRI_OVLO}		12	12.6	13.2	V
Secondary Overvoltage Lockout Response Time	t _{PRI_OVLO}			30		μs
Secondary Undervoltage Lockout Threshold	V _{SEC_UVLO} -		5.6	6	6.4	V
Secondary Undervoltage Recovery Threshold	V _{PRI_UVLO+} -		6.4	6.8	7.2	V
Secondary Undervoltage Lockout Response Time	t _{SEC_UVLO}			100		μs
Primary Output Overcurrent Trip Threshold	I _{PRI_OUT_OCP}	Powertrain is stopped but current can flow from Secondary to Primary through MOSFET body Diodes	40	44	50	А
Primary Output Overcurrent Response Time Constant	t _{PRI_OUT_OCP}	Effective internal RC filter		100		μs
Primary Short Circuit Protection Trip Threshold	I _{PRI_SCP}	Powertrain is stopped but current can flow from Secondary to Primary through MOSFET body Diodes	50			А
Primary Short Circuit Protection Response Time	t _{PRI_SCP}			1		μs



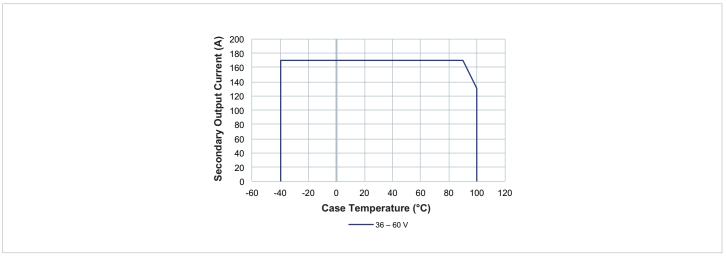


Figure 1 — Specified thermal operating area

- 1. The NBM in a VIA Package is cooled through bottom case (bottom housing).
- 2. The thermal rating of the NBM in a VIA Package is based on typical measured device efficiency.
- 3. The case temperature in the graph is the measured temperature of the bottom housing, such that operating internal junction temperature of the NBM in a VIA Package does not exceed 125°C.

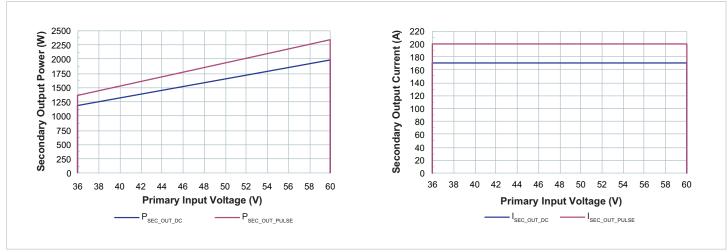


Figure 2 — Specified electrical operating area using rated R_{SEC_HOT}

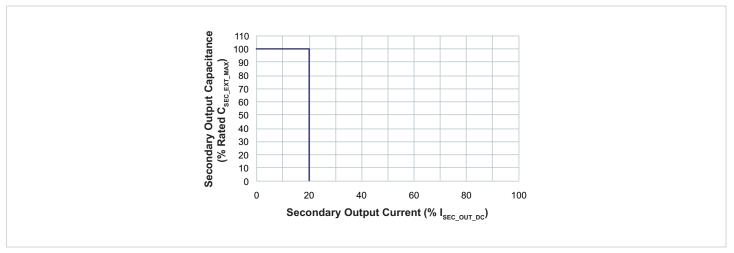
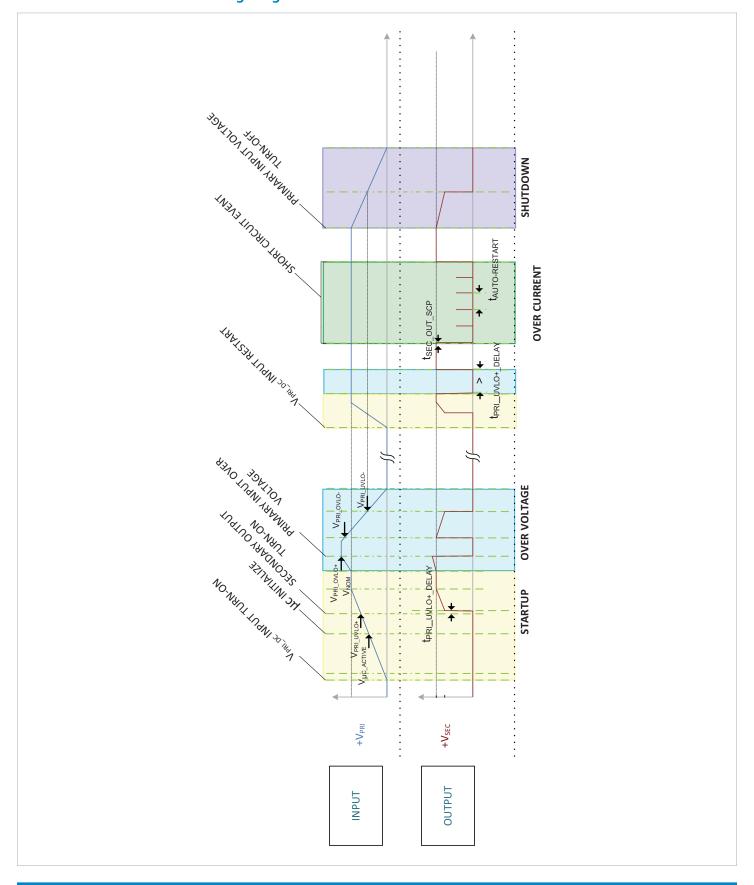


Figure 3 — Specified Primary start-up into load current and external capacitance

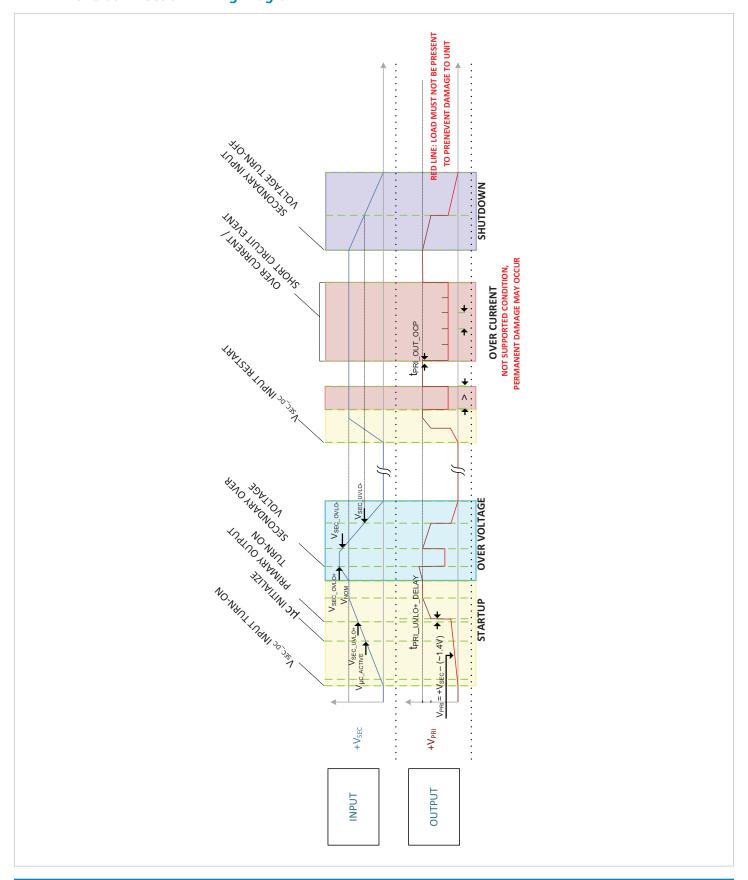


NBM™ Forward Direction Timing Diagram





NBM™ Reverse Direction Timing Diagram





Application Characteristics

Product is mounted and temperature controlled via top side cold plate, unless otherwise noted. All data presented in this section are collected data form primary sourced units processing power in forward direction. See associated figures for general trend data.

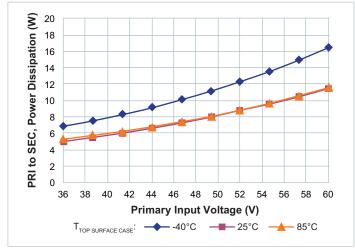


Figure 4 — No load power dissipation vs. V_{PRI_DC}

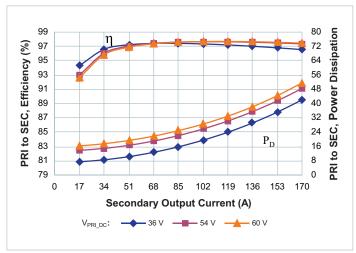


Figure 6 — Efficiency and power dissipation at $T_{CASE} = -40^{\circ}\text{C}$

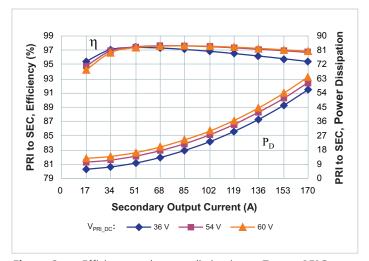


Figure 8 — Efficiency and power dissipation at $T_{CASE} = 85^{\circ}C$

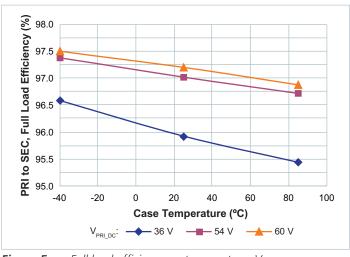


Figure 5 — Full load efficiency vs. temperature; V_{PRI_DC}

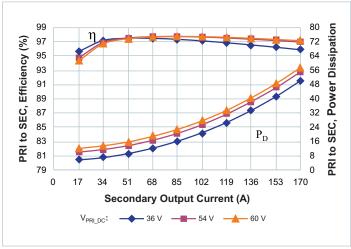


Figure 7 — Efficiency and power dissipation at $T_{CASE} = 25^{\circ}C$

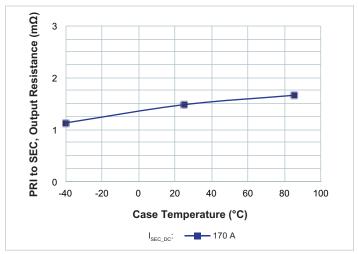


Figure 9 — R_{SEC} vs. temperature; Nominal V_{PRI_DC} $I_{SEC_DC} = 170 \text{ A}$ at $T_{CASE} = 85^{\circ}\text{C}$



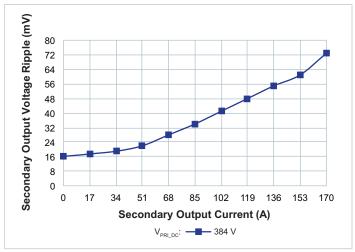


Figure 10 — $V_{SEC_OUT_PP}$ vs. I_{SEC_DC} ; No external $C_{SEC_OUT_EXT_}$ Board mounted module, scope setting : 20 MHz analog BW

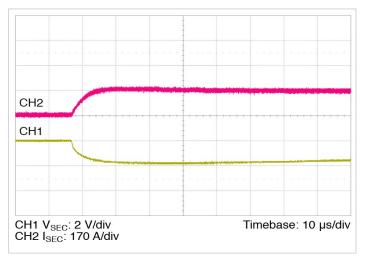


Figure 12 — 0 A– 170 A transient response: $C_{PRI_IN_EXT} = 300 \ \mu\text{F}$, no external $C_{SEC_OUT_EXT}$

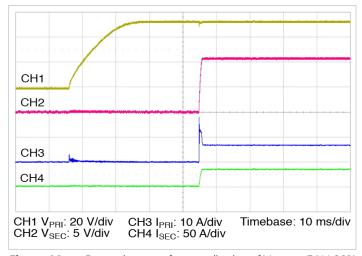


Figure 14 — Forward start up from application of V_{PRI_DC} = 54 V, 20% I_{OUT}, 100% C_{SEC_OUT_EXT}

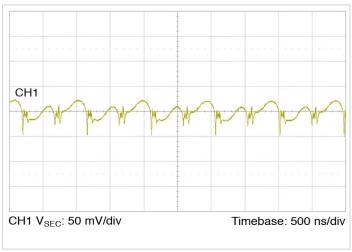


Figure 11 — Full load ripple, 300 μ F $C_{PRI_IN_EXT}$; No external $C_{SEC_OUT_EXT.}$ Board mounted module, scope setting : 20 MHz analog BW

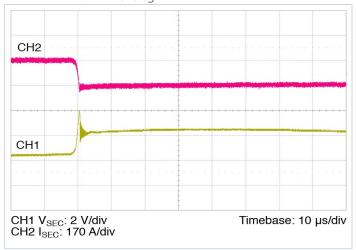


Figure 13 — 170 A – 0 A transient response: $C_{PRI_IN_EXT} = 300 \, \mu\text{F}$, no external $C_{SEC_OUT_EXT}$

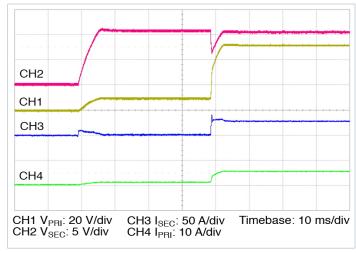


Figure 15 — Reverse start up from application of $V_{SEC_DC} = 10.8 \text{ V}, 20\% \text{ I}_{PRI_DC}, 100\% \text{ C}_{PRI_IN_EXT}$



General Characteristics

Specifications apply over all line, load conditions, unless otherwise noted; **Boldface** specifications apply over the temperature range of -40°C \leq T_{CASE} = 25°C unless otherwise noted.

Attribute	Symbol	Conditions / Notes	Min	Тур	Max	Unit
		Mechanical				
Length	L	Lug (Chassis) Mount	95.34 / [3.75]	95.59 / [3.76]	95.84 / [3.77]	mm / [in]
Length	L	PCB (Board) Mount	95.34 / [3.75]	95.59 / [3.76]	95.84 / [3.77]	mm / [in]
Width	W		35.29 / [1.39]	35.54 / [1.40]	35.79 / [1.41]	mm / [in]
Height	Н		9.019 / [0.355]	9.40 / [0.37]	9.781 / [0.385]	mm / [in]
Volume	Vol	Without heatsink		31.93 / [1.95]		cm ³ / [in ³]
Weight	W			130.4 / [4.6]		g / [oz]
Pin Material		C145 copper, 1/2 hard				
Underplate		Low stress ductile Nickel	50		100	μin
Pin Finish		Palladium	0.8		6	uin
PIII FIIIISII		Soft Gold	0.12		2	μin
		Thermal				
Operating impetion temperature	_	NBM3814x60E12A7yzz (T-Grade)	-40		125	
Operating junction temperature	T _{INTERNAL}	NBM3814x60E12A7yzz (C-Grade)	-20		125	
Operating case temperature	_	NBM3814x60E12A7yzz (T-Grade), derating applied, see safe thermal operating area	-40		100	°C
Operating case temperature	T _{CASE}	NBM3814x60E12A7yzz (C-Grade), derating applied, see safe thermal operating area	-20		100	
Thermal resistance top side	R _{JC-TOP}	Estimated thermal resistance to maximum temperature internal component from isothermal top		1.21		°C/W
Thermal Resistance Coupling between top case and bottom case	R _{HOU}	Estimated thermal resistance of thermal coupling between the top and bottom case surfaces		0.47		°C/W
Thermal resistance bottom side	R _{JC-BOT}	Estimated thermal resistance to maximum temperature internal component from isothermal bottom		0.70		°C/W
Thermal capacity				52		Ws/°C
		Assembly				
C. T.	_	NBM3814x60E12A7yzz (T-Grade)	-40		125	°C
Storage Temperature	T _{ST}	NBM3814x60E12A7yzz (C-Grade)	-40		125	°C
ESD Withstand	ESD _{HBM}	Human Body Model, "ESDA / JEDEC JDS-001-2012" Class I-C (1kV to < 2 kV)	1000			
LSD WITHStalia	ESD _{CDM}	Charge Device Model, "JESD 22-C101-E" Class II (200V to < 500V)	200			



General Characteristics (Cont.)

Specifications apply over all line, load conditions, unless otherwise noted; **Boldface** specifications apply over the temperature range of -40°C \leq T_{CASE} = 25°C unless otherwise noted.

Attribute	Symbol	Conditions / Notes	Min	Тур	Max	Unit
		Safety				
Isolation capacitance	CIN_OUT	Unpowered unit	N/A	N/A	N/A	pF
Isolation resistance	RIN_OUT	At 500 Vdc	0			МΩ
MTBF		MIL-HDBK-217Plus Parts Count - 25°C Ground Benign, Stationary, Indoors / Computer		2.2		MHrs
		Telcordia Issue 2 - Method I Case III; 25°C Ground Benign, Controlled		3.6		MHrs
Agency approvals / standards		CE Marked for Low Voltage Directive and	l RoHS Recast Di	rective, as applic	cable	



NBM in a VIA Package

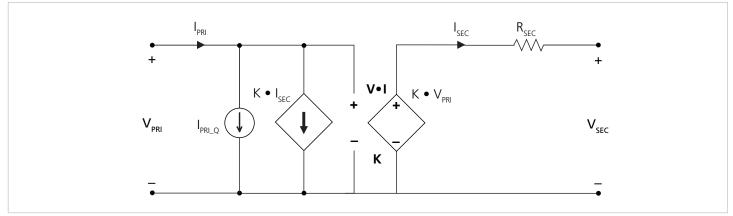


Figure 16 - NBM DC model

The NBM in a VIA package uses a high frequency resonant tank to move energy from Primary to secondary and vice versa. (The resonant tank is formed by Cr and leakage inductance Lr in the power transformer windings as shown in the NBM module Block Diagram). The resonant LC tank, operated at high frequency, is amplitude modulated as a function of input voltage and output current. A small amount of capacitance embedded in the primary and secondary stages of the module is sufficient for full functionality and is key to achieving high power density.

The NBM3814x60E12A7yzz can be simplified into the preceeding model.

At no load:

$$V_{SEC} = V_{PRI} \bullet K \tag{1}$$

K represents the "turns ratio" of the NBM. Rearranging Eq (1):

$$K = \frac{V_{SEC}}{V_{PRI}} \tag{2}$$

In the presence of load, V_{SEC} is represented by:

$$V_{SEC} = V_{PRI} \bullet K - I_{SEC} \bullet R_{SEC} \tag{3}$$

and $\boldsymbol{I}_{\text{SEC}}$ is represented by:

$$I_{SEC} = \frac{I_{PRI} - I_{PRI_Q}}{K} \tag{4}$$

 $R_{\rm SEC}$ represents the impedance of the NBM, and is a function of the $R_{\rm DSON}$ of the input and output MOSFETs, PC board resistance of input and output boards and the winding resistance of the power transformer. $I_{\rm Q}$ represents the quiescent current of the NBM control, gate drive circuitry, and core losses.

The use of DC voltage transformation provides additional interesting attributes. Assuming that R_{SEC} = 0 Ω and $I_{PRL,Q}$ = 0 A, Eq. (3) now becomes Eq. (1) and is essentially load independent, resistor R is now placed in series with V_{PRI} .

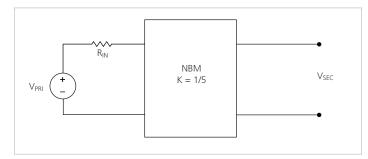


Figure 17 — K = 1/5 NBM with series input resistor

The relationship between V_{PRI} and V_{SEC} becomes:

$$V_{SEC} = (V_{PRI} - I_{PRI} \cdot R_{IN}) \cdot K \tag{5}$$

Substituting the simplified version of Eq. (4) $(I_{PRI_Q} \text{ is assumed} = 0 \text{ A}) \text{ into Eq. (5) yields:}$

$$V_{SEC} = V_{PRI} \cdot K - I_{SEC} \cdot R_{IN} \cdot K^2 \tag{6}$$



This is similar in form to Eq. (3), where R_{SEC} is used to represent the characteristic impedance of the NBMTM. However, in this case a real R on the primary side of the NBM is effectively scaled by K^2 with respect to the secondary.

Assuming that R = 1 Ω , the effective R as seen from the secondary side is 40 m Ω , with K = 1/5 .

A similar exercise should be performed with the addition of a capacitor or shunt impedance at the primary input to the NBM. A switch in series with V_{PRI} is added to the circuit. This is depicted in Figure 18.



Figure 18 — NBM with input capacitor

A change in V_{PRI} with the switch closed would result in a change in capacitor current according to the following equation:

$$I_C(t) = C \frac{dV_{PRI}}{dt} \tag{7}$$

Assume that with the capacitor charged to V_{PRI} , the switch is opened and the capacitor is discharged through the idealized NBM. In this case,

$$I_C = I_{SEC} \circ K \tag{8}$$

substituting Eq. (1) and (8) into Eq. (7) reveals:

$$I_{SEC} = \frac{C}{K^2} \bullet \frac{dI_{SEC}}{dt} \tag{9}$$

The equation in terms of the output has yielded a K^2 scaling factor for C, specified in the denominator of the equation.

A K factor less than unity results in an effectively larger capacitance on the secondary output when expressed in terms of the input. With a K= 1/5 as shown in Figure 18, C=1 μF would appear as C=25 μF when viewed from the secondary.

Low impedance is a key requirement for powering a high-current, low-voltage load efficiently. A switching regulation stage should have minimal impedance while simultaneously providing appropriate filtering for any switched current. The use of a NBM between the regulation stage and the point of load provides a dual benefit of scaling down series impedance leading back to the source and scaling up shunt capacitance or energy storage as a function of its K factor squared. However, the benefits are not useful if the series impedance of the NBM is too high. The impedance of the NBM must be low, i.e. well beyond the crossover frequency of the system.

A solution for keeping the impedance of the NBM low involves switching at a high frequency. This enables small magnetic components because magnetizing currents remain low. Small magnetics mean small path lengths for turns. Use of low loss core material at high frequencies also reduces core losses.

The two main terms of power loss in the NBM module are:

- No load power dissipation (P_{PRI_NL}): defined as the power used to power up the module with an enabled powertrain at no load.
- Resistive loss (R_{SEC}): refers to the power loss across the NBM module modeled as pure resistive impedance.

$$P_{DISSIPATED} = P_{PRI_NL} + P_{R_{SFC}} \tag{10}$$

Therefore,

$$P_{SEC_OUT} = P_{PRI_IN} - P_{DISSIPATED} = P_{PRI_IN} - P_{PRI_NL} - P_{RSFC}$$
 (11)

The above relations can be combined to calculate the overall module efficiency:

$$\eta = \frac{P_{SEC_OUT}}{P_{PRI_IN}} = \frac{P_{PRI_IN} - P_{PRI_NL} - P_{RSEC}}{P_{PRI_IN}}$$
(12)

$$= \ \ \frac{V_{PRI} \bullet I_{PRI} - P_{PRI_NL} - (I_{SEC})^2 \bullet R_{SEC}}{V_{PRI} \bullet I_{PRI}}$$

$$= 1 - \left(\frac{P_{PRI_NL} + (I_{SEC})^2 \cdot R_{SEC}}{V_{PRI} \cdot I_{PRI}} \right)$$



Input and Output Filter Design

A major advantage of NBM systems versus conventional PWM converters is that the transformer based NBM does not require external filtering to function properly. The resonant LC tank, operated at extreme high frequency, is amplitude modulated as a function of input voltage and output current and efficiently transfers charge through the isolation transformer. A small amount of capacitance embedded in the primary and secondary stages of the module is sufficient for full functionality and is key to achieving power density.

This paradigm shift requires system design to carefully evaluate external filters in order to:

- Guarantee low source impedance:
 - To take full advantage of the NBM module's dynamic response, the impedance presented to its input terminals must be low from DC to approximately 5 MHz. The connection of the bus converter module to its power source should be implemented with minimal distribution inductance. If the interconnect inductance exceeds 100 nH, the input should be bypassed with a RC damper to retain low source impedance and stable operation. With an interconnect inductance of 200 nH, the RC damper may be as high as 1 μF in series with 0.3 Ω . A single electrolytic or equivalent low-Q capacitor may be used in place of the series RC bypass.
- Further reduce input and/or output voltage ripple without sacrificing dynamic response:
 - Given the wide bandwidth of the module, the source response is generally the limiting factor in the overall system response. Anomalies in the response of the source will appear at the output of the module multiplied by its K factor.
- Protect the module from overvoltage transients imposed by the system that would exceed maximum ratings and induce stresses:

The module primary/secondary voltage ranges shall not be exceeded. An internal overvoltage lockout function prevents operation outside of the normal operating input range. Even when disabled, the powertrain is exposed to the applied voltage and power MOSFETs must withstand it.

Total load capacitance at the output of the NBM module shall not exceed the specified maximum. Owing to the wide bandwidth and low output impedance of the module, low-frequency bypass capacitance and significant energy storage may be more densely and efficiently provided by adding capacitance at the input of the module. At frequencies <500 kHz the module appears as an impedance of R_{SEC} between the source and load.

Within this frequency range, capacitance at the input appears as effective capacitance on the output per the relationship defined in Eq. (13).

$$C_{SEC_EXT} = \frac{C_{PRI_EXT}}{K^2}$$
 (13)

This enables a reduction in the size and number of capacitors used in a typical system.

Thermal Considerations

The VIA™ package provides effective conduction cooling from either of the two module surfaces. Heat may be removed from the top surface, the bottom surface or both. The extent to which these two surfaces are cooled is a key component for determining the maximum power that can be processed by a VIA, as can be seen from specified thermal operating area in Figure 1. Since the VIA has a maximum internal temperature rating, it is necessary to estimate this internal temperature based on a system-level thermal solution. To this purpose, it is helpful to simplify the thermal solution into a roughly equivalent circuit where power dissipation is modeled as a current source, isothermal surface temperatures are represented as voltage sources and the thermal resistances are represented as resistors. Figure 19 shows the "thermal circuit" for the VIA module.

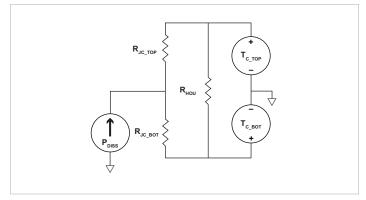


Figure 19 - Double sided cooling VIA thermal model

In this case, the internal power dissipation is P_{DISS} , R_{JC_TOP} and R_{JC_BOT} are thermal resistance characteristics of the VIA module and the top and bottom surface temperatures are represented as T_{C_TOP} , and T_{C_BOT} . It interesting to notice that the package itself provides a high degree of thermal coupling between the top and bottom case surfaces (represented in the model by the resistor R_{HOU}). This feature enables two main options regarding thermal designs:

■ Single side cooling: the model of Figure 19 can be simplified by calculating the parallel resistor network and using one simple thermal resistance number and the internal power dissipation curves; an example for bottom side cooling only is shown in Figure 20.

In this case, R_{JC} can be derived as following:

$$R_{JC} = \frac{(R_{JC_TOP} + R_{HOU}) \cdot R_{JC_BOT}}{R_{JC_TOP} + R_{HOU} + R_{JC_BOT}}$$
(14)



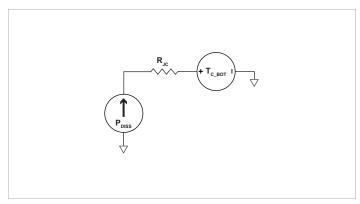


Figure 20 – Single-sided cooling VIA thermal model

Double side cooling: while this option might bring limited advantage to the module internal components (given the surface-to-surface coupling provided), it might be appealing in cases where the external thermal system requires allocating power to two different elements, like for example heatsinks with independent airflows or a combination of chassis/air cooling.

Current Sharing

The performance of the NBM in a VIA package is based on efficient transfer of energy through a transformer without the need of closed loop control. For this reason, the transfer characteristic can be approximated by an ideal transformer with a positive temperature coefficient series resistance.

This type of characteristic is close to the impedance characteristic of a DC power distribution system both in dynamic (AC) behavior and for steady state (DC) operation.

When multiple NBM modules of a given part number are connected in an array they will inherently share the load current according to the equivalent impedance divider that the system implements from the power source to the point of load.

Some general recommendations to achieve matched array impedances include:

- Dedicate common copper planes/wires within the PCB/Chassis to deliver and return the current to the VIA modules.
- Provide as symmetric a PCB/Wiring layout as possible among VIA™ modules

For further details see <u>AN:016 Using BCM Bus Converters</u> in High Power Arrays.

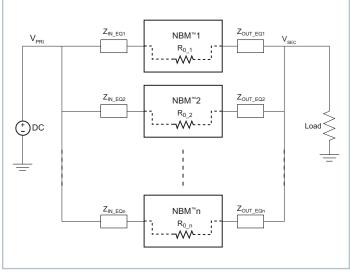


Figure 21 — NBM module array

Fuse Selection

In order to provide flexibility in configuring power systems, NBM in a VIA package modules are not internally fused. Input line fusing of NBM in a VIA package products is recommended at system level to provide thermal protection in case of catastrophic failure.

The fuse shall be selected by closely matching system requirements with the following characteristics:

- Current rating (usually greater than maximum current of NBM module)
- Maximum voltage rating (usually greater than the maximum possible input voltage)
- Ambient temperature
- Nominal melting I²t
- Recommend fuse: ≤60 A Littelfuse TLS Series or Littlefuse 456 series rated 40 A

Startup and Reverse Operation

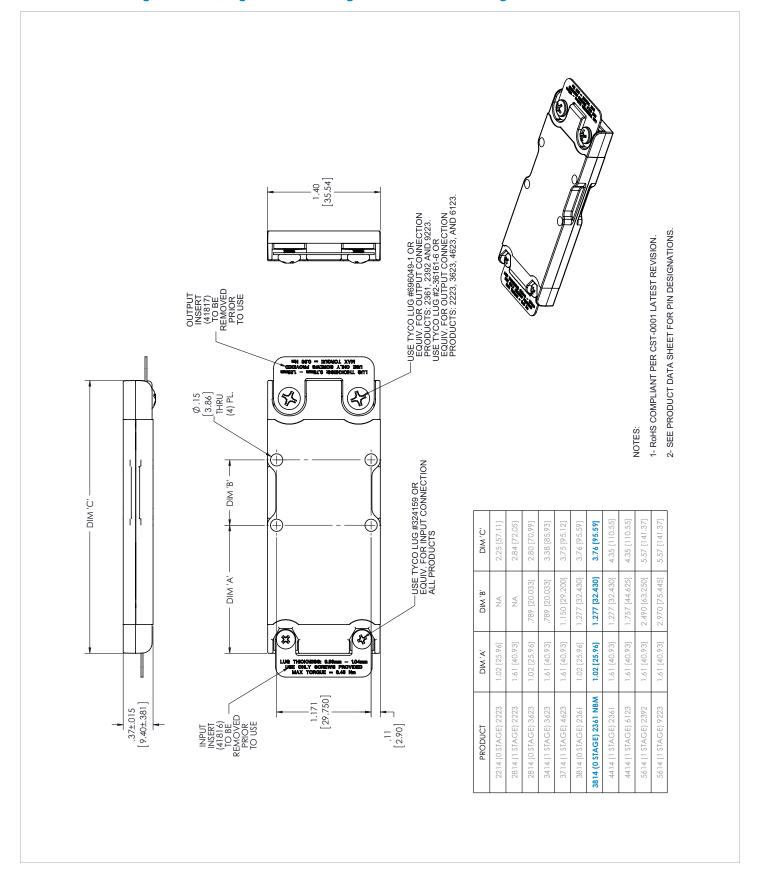
The NBM3814x60E12A7yzz is capable of startup in forward and reverse direction once the applied voltage is greater than the undervoltage lockout threshold.

The non-isolated bus converter modules are capable of reverse power operation. Once the unit is enabled, energy can be transferred from secondary back to the primary whenever the secondary voltage exceeds $V_{PRI} \bullet K$. The module will continue operation in this fashion for as long as no faults occur.

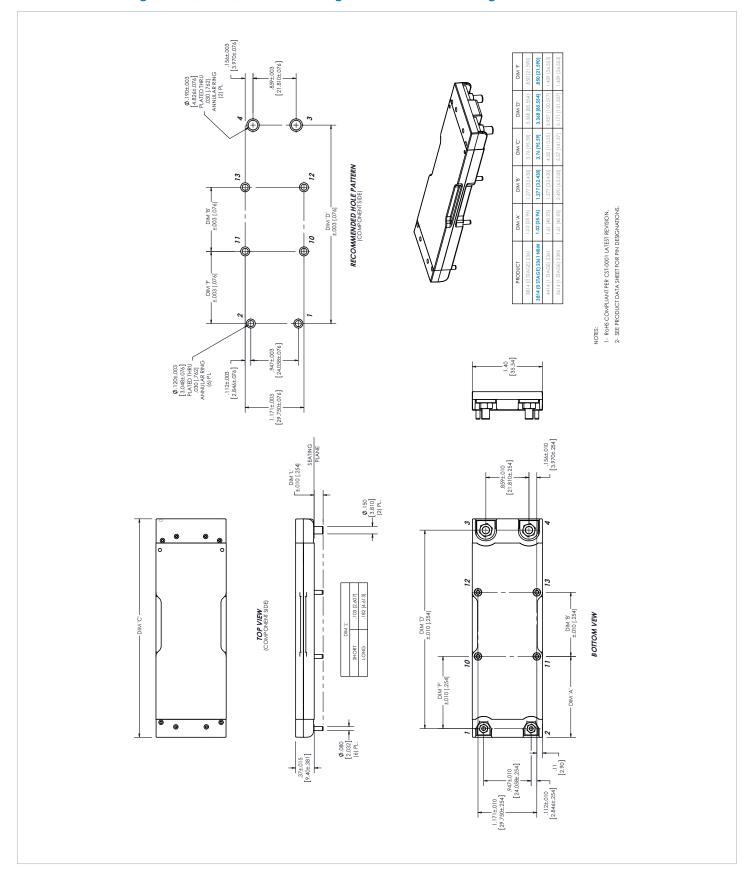
Startup loading could be set to no greater than 20% of rated max current respectively in forward or reverse direction. A load must not be present on the +V_{PRI} pin if the powertrain is not actively switching. Remove +PRI load prior to disabling the module using +SEC power or prior to faults. Primary MOSEFT body diode conduction will occur if unit stops switching while a load is present on the +V_{PRI} and +V_{SEC} voltage is two diodes drop higher than +V_{PRI}.



NBM in VIA Package Chassis (Lug) Mount Package Mechanical Drawing



NBM in VIA Package PCB (Board) Mount Package Mechanical Drawing and Recommended Hole Pattern



Revision History

Revision	Date	Description	Page Number(s)
1.0	03/3/16	Initial release	n/a



Vicor's comprehensive line of power solutions includes high density AC-DC and DC-DC modules and accessory components, fully configurable AC-DC and DC-DC power supplies, and complete custom power systems.

Information furnished by Vicor is believed to be accurate and reliable. However, no responsibility is assumed by Vicor for its use. Vicor makes no representations or warranties with respect to the accuracy or completeness of the contents of this publication. Vicor reserves the right to make changes to any products, specifications, and product descriptions at any time without notice. Information published by Vicor has been checked and is believed to be accurate at the time it was printed; however, Vicor assumes no responsibility for inaccuracies. Testing and other quality controls are used to the extent Vicor deems necessary to support Vicor's product warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

Specifications are subject to change without notice.

Vicor's Standard Terms and Conditions

All sales are subject to Vicor's Standard Terms and Conditions of Sale, which are available on Vicor's webpage or upon request.

Product Warranty

In Vicor's standard terms and conditions of sale, Vicor warrants that its products are free from non-conformity to its Standard Specifications (the "Express Limited Warranty"). This warranty is extended only to the original Buyer for the period expiring two (2) years after the date of shipment and is not transferable.

UNLESS OTHERWISE EXPRESSLY STATED IN A WRITTEN SALES AGREEMENT SIGNED BY A DULY AUTHORIZED VICOR SIGNATORY, VICOR DISCLAIMS ALL REPRESENTATIONS, LIABILITIES, AND WARRANTIES OF ANY KIND (WHETHER ARISING BY IMPLICATION OR BY OPERATION OF LAW) WITH RESPECT TO THE PRODUCTS, INCLUDING, WITHOUT LIMITATION, ANY WARRANTIES OR REPRESENTATIONS AS TO MERCHANTABILITY, FITNESS FOR PARTICULAR PURPOSE, INFRINGEMENT OF ANY PATENT, COPYRIGHT, OR OTHER INTELLECTUAL PROPERTY RIGHT, OR ANY OTHER MATTER.

This warranty does not extend to products subjected to misuse, accident, or improper application, maintenance, or storage. Vicor shall not be liable for collateral or consequential damage. Vicor disclaims any and all liability arising out of the application or use of any product or circuit and assumes no liability for applications assistance or buyer product design. Buyers are responsible for their products and applications using Vicor products and components. Prior to using or distributing any products that include Vicor components, buyers should provide adequate design, testing and operating safeguards.

Vicor will repair or replace defective products in accordance with its own best judgment. For service under this warranty, the buyer must contact Vicor to obtain a Return Material Authorization (RMA) number and shipping instructions. Products returned without prior authorization will be returned to the buyer. The buyer will pay all charges incurred in returning the product to the factory. Vicor will pay all reshipment charges if the product was defective within the terms of this warranty.

Life Support Policy

VICOR'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS PRIOR WRITTEN APPROVAL OF THE CHIEF EXECUTIVE OFFICER AND GENERAL COUNSEL OF VICOR CORPORATION. As used herein, life support devices or systems are devices which (a) are intended for surgical implant into the body, or (b) support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in a significant injury to the user. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system or to affect its safety or effectiveness. Per Vicor Terms and Conditions of Sale, the user of Vicor products and components in life support applications assumes all risks of such use and indemnifies Vicor against all liability and damages.

Intellectual Property Notice

Vicor and its subsidiaries own Intellectual Property (including issued U.S. and Foreign Patents and pending patent applications) relating to the products described in this data sheet. No license, whether express, implied, or arising by estoppel or otherwise, to any intellectual property rights is granted by this document. Interested parties should contact Vicor's Intellectual Property Department.

The products described on this data sheet are protected by the following U.S. Patents Pending

Vicor Corporation

25 Frontage Road Andover, MA, USA 01810 Tel: 800-735-6200 Fax: 978-475-6715

email

Customer Service: custserv@vicorpower.com
Technical Support: apps@vicorpower.com

